Silicon NPN Power Transistors BUV70

DESCRIPTION

·With TO-3PN package
·High breakdown voltage
·Fast switching speed
·Wide area of safe operation

APPLICATIONS

·For switching regulator applications

PINNING

PIN	DESCRIPTION
1	Base
2	Collector;connected to mounting base
3	Emitter

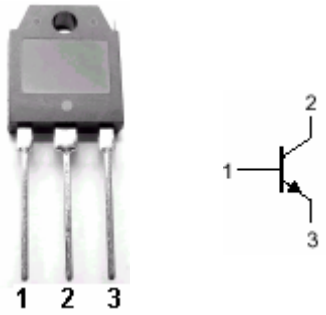

Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings (Ta=25□)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1300	V
V_{CEO}	Collector-emitter voltage	Open base	550	V
V_{EBO}	Emitter-base voltage	Open collector	7	V
I_C	Collector current		10	A
I_B	Base current		4	A
P_C	Collector power dissipation	T_C=25□	140	W
T_j	Junction temperature		150	□
T_{stg}	Storage temperature		-55~150	□

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CHARACTERISTICS

Tj=25□ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{(BR)CEO}$	Collector-emitter breakdown voltage	I_C=5mA ;I_B=0	550			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	I_E=1mA ;I_C=0	7			V
V_{CEsat}	Collector-emitter saturation voltage	I_C=6A; I_B=1.2A			2.0	V
V_{BEsat}	Base-emitter saturation voltage	I_C=6A; I_B=1.2A			1.5	V
I_{CBO}	Collector cut-off current	V_{CB}=500V; I_E=0			10	μA
I_{EBO}	Emitter cut-off current	V_{EB}=5V; I_C=0			10	μA
h_{FE}	DC current gain	I_C=3.2A ; V_{CE}=2V	5			
f_T	Transition frequency	I_C=0.5A ; V_{CE}=10V		9		MHz

PACKAGE OUTLINE

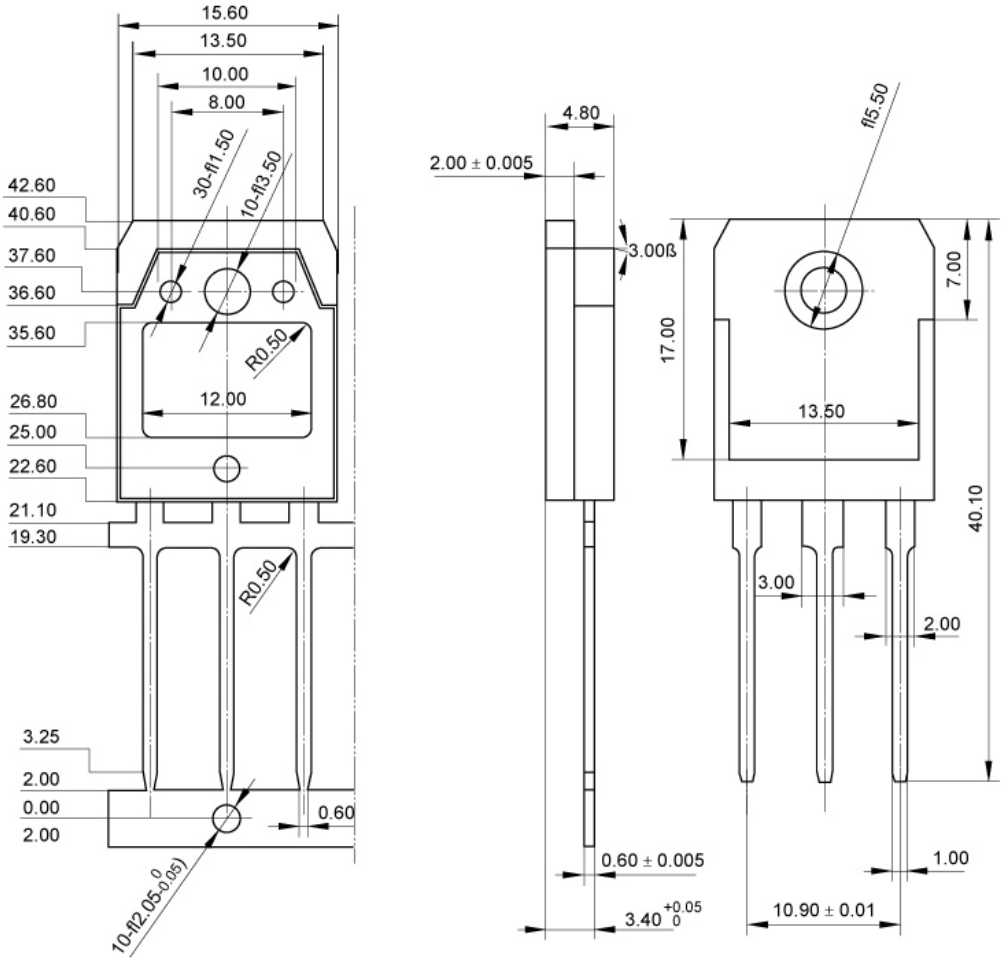

Fig.2 outline dimensions